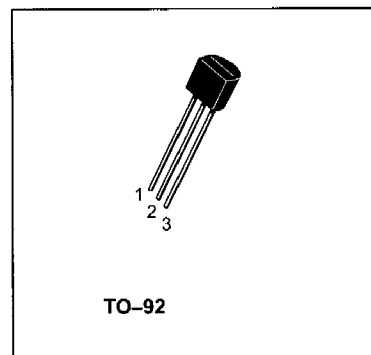
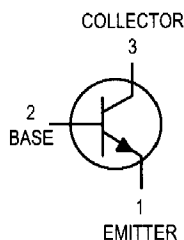


## Amplifier Transistor

### NPN Silicon

**MPS6530**



#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	40	Vdc
Collector–Base Voltage	$V_{CBO}$	60	Vdc
Emitter–Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current — Continuous	$I_C$	600	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625	mW
Junction Temperature	$T_J, T_{stg}$	150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.2	$^\circ\text{C}/\text{mW}$

#### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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#### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ( $I_C = 10 \text{ mAdc}, I_B = 0$ )	$V_{(BR)CEO}$	40	—	Vdc
Collector–Base Breakdown Voltage ( $I_C = 10 \mu\text{Adc}, I_E = 0$ )	$V_{(BR)CBO}$	60	—	Vdc
Emitter–Base Breakdown Voltage ( $I_B = 10 \mu\text{Adc}, I_C = 0$ )	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ( $V_{CB} = 40 \text{ Vdc}, I_E = 0$ ) ( $V_{CB} = 40 \text{ Vdc}, I_E = 0, T_A = 60^\circ\text{C}$ )	$I_{CBO}$	—	0.05 2.0	$\mu\text{Adc}$



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# MPS6530

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>ON CHARACTERISTICS</b>				
DC Current Gain (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 100 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 500 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> )	h <sub>FE</sub>	30 40 25	— 120 —	—
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 100 mA <sub>dc</sub> , I <sub>B</sub> = 10 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	—	0.5	V <sub>dc</sub>
Base–Emitter Saturation Voltage (I <sub>C</sub> = 100 mA <sub>dc</sub> , I <sub>B</sub> = 10 mA <sub>dc</sub> )	V <sub>BE(sat)</sub>	—	1.0	V <sub>dc</sub>
<b>SMALL–SIGNAL CHARACTERISTICS</b>				
Output Capacitance (V <sub>CB</sub> = 10 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	—	5.0	pF

### SWITCHING TIME EQUIVALENT TEST CIRCUITS

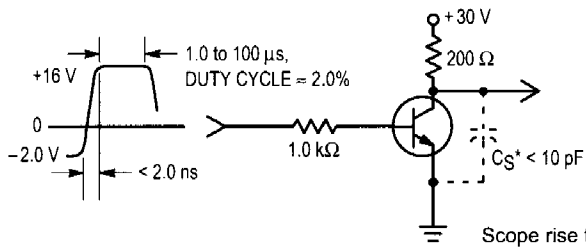


Figure 1. Turn–On Time

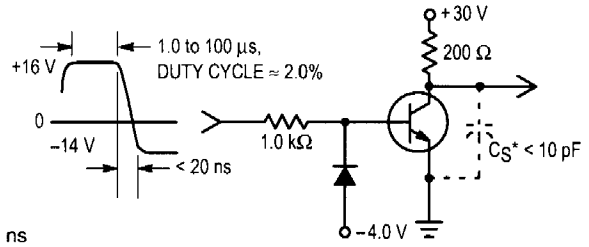


Figure 2. Turn–Off Time

Scope rise time < 4.0 ns

\*Total shunt capacitance of test jig connectors, and oscilloscope